

- Alguno, A; Usami, N; Ujihara, T; Fujiwara, K; Sazaki, G; Nakajima, K; Shiraki, Y  
*Enhanced quantum efficiency of solar cells with self-assembled Ge dots stacked in multilayer structure*  
Appl. Phys. Lett. 83 (2003) 1258 – 1260  
03-IMR0037
- 
- Zhang, BP; Binh, NT; Segawa, Y; Wakatsuki, K; Usami, N  
*Optical properties of ZnO rods formed by metalorganic chemical vapor deposition*  
Appl. Phys. Lett. 83 (2003) 1635 – 1637  
03-IMR0038
- 
- Sawano, K; Koh, S; Shiraki, Y; Usami, N; Nakagawa, K  
*In-plane strain fluctuation in strained-Si/SiGe heterostructures*  
Appl. Phys. Lett. 83 (2003) 4339 – 4341  
03-IMR0039
- 
- Shishido, T; Ye, JH; Okada, S; Kudou, K; Iizumi, K; Oku, M; Ishizawa, Y; Amano, T; Kohiki, S; Kawazoe, Y; Nakajima, K  
*Hardness and oxidation resistance of perovskite-type borocarbide system  $YR_h3B_xC_{1-x}$  ( $0 \leq x \leq 1$ )*  
J. Alloy. Compd. 354 (2003) 198 – 201  
03-IMR0040
- 
- Oku, M; Shishido, T; Sun, Q; Nakajima, K; Kawazoe, Y; Wagatsuma, K  
*Comparison of electronic structures of ScAl3 and ScRh3: X-ray photoelectron spectroscopy and ab initio band calculation*  
J. Alloy. Compd. 358 (2003) 264 – 267  
03-IMR0041
- 
- Usami, N; Ichitsubo, T; Ujihara, T; Takahashi, T; Fujiwara, K; Sazaki, G; Nakajima, K  
*Influence of the elastic strain on the band structure of ellipsoidal SiGe coherently embedded in the Si matrix*  
J. Appl. Phys. 94 (2003) 916 – 920  
03-IMR0042
- 
- Azuma, Y; Usami, N; Ujihara, T; Fujiwara, K; Sazaki, G; Murakami, Y; Nakajima, K  
*Growth of SiGe bulk crystals with uniform composition by utilizing feedback control system of the crystal-melt interface position for precise control of the growth temperature*  
J. Cryst. Growth 250 (2003) 298 – 304  
03-IMR0043
- 
- Sawano, K; Arimoto, K; Hirose, Y; Koh, S; Usami, N; Nakagawa, K; Hattori, T; Shiraki, Y  
*Planarization of SiGe virtual substrates by CMP and its application to strained Si modulation-doped structures*  
J. Cryst. Growth 251 (2003) 693 – 696  
03-IMR0044
- 
- Nagatoshi, Y; Sazaki, G; Suzuki, Y; Miyashita, S; Matsui, T; Ujihara, T; Fujiwara, K; Usami, N; Nakajima, K  
*Effects of high pressure on the growth kinetics of orthorhombic lysozyme crystals*  
J. Cryst. Growth 254 (2003) 188 – 195  
03-IMR0045
-

Yanagiya, S; Nishikata, S; Sazaki, G; Hoshino, A; Nakajima, K; Inoue, T  
*Recrystallization of Cu-phthalocyanine on KCl (001) substrates by annealing method*  
J. Cryst. Growth 254 (2003) 244 – 250

03-IMR0046

Mikami, M; Nakamura, S; Itoh, M; Nakajima, K; Shishido, T  
*Lattice dynamics and optical properties of yttrium oxysulfide*  
J. Lumines. 102 (2003) 7 – 12

03-IMR0047

Hayashi, K; Takahashi, Y; Matsubara, E; Nakajima, K; Usami, N  
*3D atomic imaging of SiGe system by X-ray fluorescence holography*  
J. Mater. Sci.-Mater. Electron. 14 (2003) 459 – 462

03-IMR0048

Zhang, BP; Manh, LH; Wakatsuki, K; Ohnishi, T; Lippmaa, M; Usami, N; Kawasaki, M; Segawa, Y  
*Epitaxial growth and polarity of ZnO films on sapphire (0001) substrates by low-pressure metal organic chemical vapor deposition*  
Jpn. J. Appl. Phys. Part 1 – Regul. 42 (2003) 2291 – 2295  
Pap. Short Notes Rev. Pap.

03-IMR0049

Shishido, T; Ye, JH; Kudou, K; Okada, S; Iizumi, K; Oku, M; Ishizawa, Y; Yoshikawa, A; Tanaka, M; Oishi, S; Kamegashira, N; Kohiki, S; Kawazoe, Y; Nakajima, K  
*Hardness and oxidation resistance of perovskite-type solid solution of the ScRh3B-ScRh3C system*  
Jpn. J. Appl. Phys. Part 1 – Regul. 42 (2003) 5213 – 5214  
Pap. Short Notes Rev. Pap.

03-IMR0050

Shishido, T; Okada, S; Ishizawa, Y; Kudou, K; Iizumi, K; Sawada, Y; Horiuchi, H; Inaba, K; Sekiguchi, T; Ye, JH; Miyashita, S; Nomura, A; Sugawara, T; Obara, K; Murakami, Y; Fujiwara, K; Ujihara, T; Sazaki, G; Usami, N; Oku, M; Yokoyama, Y; Kohiki, S; Kawazoe, Y; Nakajima, K  
*High-temperature solution growth and characterization of chromium disilicide*  
Jpn. J. Appl. Phys. Part 1 – Regul. 42 (2003) 7292 – 7293  
Pap. Short Notes Rev. Pap.

03-IMR0051

Shishido, T; Kudou, K; Sasaki, T; Okada, S; Ye, JH; Iizumi, K; Nomura, A; Sugawara, T; Obara, K; Tanaka, M; Kohiki, S; Kawazoe, Y; Nakajima, K; Oku, M  
*Search for perovskite-type new boride in the Sc-Ni-B system*  
Jpn. J. Appl. Phys. Part 1 – Regul. 42 (2003) 7464 – 7466  
Pap. Short Notes Rev. Pap.

03-IMR0052

Ujihara, T; Obara, K; Usami, N; Fujiwara, K; Sazaki, G; Shishido, T; Nakajima, K  
*High-quality crystalline silicon layer grown by liquid phase epitaxy method at low growth temperature*  
Jpn. J. Appl. Phys. Part 2 – Lett. 42 (2003) L217 – L219

03-IMR0053

Kutsukake, K; Usami, N; Fujiwara, K; Ujihara, T; Sazaki, G; Zhang, BP; Segawa, Y; Nakajima, K  
*Fabrication of SiGe-on-insulator through thermal diffusion of Ge on Si-on-insulator substrate*  
Jpn. J. Appl. Phys. Part 2 – Lett. 42 (2003) L232 – L234

03-IMR0054

Zhang, BP; Manh, L; Wakatsuki, K; Tamura, K; Ohnishi, T; Lippma, M; Usami, N; Kawasaki, M; Koinuma, H; Segawa, Y

*In-plane orientation and polarity of ZnO epitaxial films on As-polished sapphire ( $\alpha$ -Al<sub>2</sub>O<sub>3</sub>) (0001) substrates grown by metal organic chemical vapor deposition*

Jpn. J. Appl. Phys. Part 2 – Lett. 42 (2003) L264 – L266

03-IMR0055

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